Discrete IGBTs Silicon N-Channel IGBT

GT30J65MRB

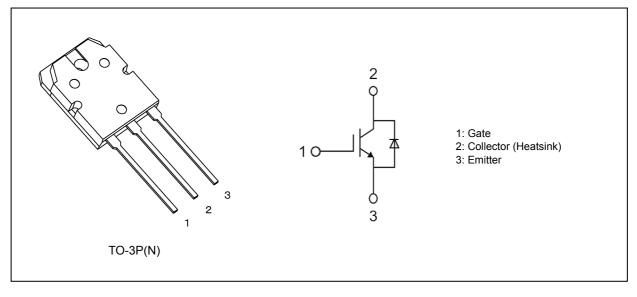
1. Applications

• Power Factor Correction (PFC)

2. Features

- (1) 7th generation
- (2) The RC-IGBT consists of a freewheeling diode (FWD) monolithically integrated in an IGBT chip.
- (3) Enhancement mode
- (4) High-speed switching: t_f = 40 ns (typ.) (I_C = 15 A, R_G = 56 Ω)
- (5) Low saturation voltage: $V_{CE(sat)} = 1.40 \text{ V}$ (typ.) (I_C = 30 A)
- (6) High junction temperature: $T_j = 175 \text{ °C} (max)$

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25$ °C, unless otherwise specified)

Characteristics		Symbol	Test Condition	Rating	Unit
Collector-emitter voltage	(Note1)	V _{CES}		650	V
Gate-emitter voltage		V _{GES}		±25	V
Collector current (DC)		Ι _C	(T _c = 25 °C)	60	A
			(T _c = 100 °C)	30]
Collector current (1 ms)		I _{CP}		120	A
Diode forward current (DC)		I _F	(T _c = 25 °C)	30	A
			(T _c = 100 °C)	15	1
Diode forward current (100 μs)		I _{FP}		60	A
Collector power dissipation		P _C	(T _c = 25 °C)	200	W
Junction temperature	(Note1)	Tj		175	°C
Storage temperature		T _{stg}		-55 to 175	°C
Mounting torque		TOR		0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note1: To perform derating ensures the device reliability.

In operation, the collector emitter voltage(V_{CES}) should be below 550 V, as well as junction temperature(T_j) should be below 140 °C.

5. Thermal Characteristics

Characteristics	Symbol	Мах	Unit
Junction-to-case thermal resistance	R _{th(j-c)}	0.75	°C/W

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25$ °C, unless otherwise specified)

Characteristics	Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current	I _{GES}	V_{GE} = ±25 V, V_{CE} = 0 V		_	_	±100	nA
Collector cut-off current	I _{CES}	V _{CE} = 650 V, V _{GE} = 0 V		_	_	10	μA
Gate-emitter cut-off voltage	V _{GE(OFF)}	V _{CE} = 5 V, I _C = 30 mA		4.2	_	6.2	V
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 30 A, V _{GE} = 15 V,	T _c = 25 °C	_	1.40	1.80	V
		(pulse test)	T _c = 175 °C	_	1.65	_	

6.2. Dynamic Characteristics (T_a = 25 °C, unless otherwise specified)

Characteristics	Symbol	Test Condition		Min	Тур.	Max	Unit
Input capacitance	C _{ies}	V _{CE} = 25 V, V _{GE} = 0 V,		_	2150	_	pF
Reverse transfer capacitance	C _{res}	f = 100 kHz	f = 100 kHz		18	_	
Output capacitance	C _{oes}			_	45	_	
Total gate charge	Qg	V_{CE} = 520 V, V_{GE} = 15 V, I _C = 30 A		_	70	—	nC
Switching time (turn-on delay time)	t _{d(on)}	Inductive load $V_{CE} = 400 \text{ V}, I_C = 15 \text{ A},$	T _c = 25 °C	_	75	—	ns
		V_{GE} = 15 V, R_{G} = 56 Ω See Fig. 6.2.1, 6.2.2	T _c = 175 °C		70	—	
Switching time (rise time)	t _r Inductive load $V_{CE} = 400 \text{ V}, I_C = 15 \text{ A},$	T _c = 25 °C		25	_	ns	
		V_{GE} = 15 V, R_{G} = 56 Ω See Fig. 6.2.1, 6.2.2	T _c = 175 °C		25	—	
Switching time (turn-off delay time)	t _{d(off)}	Inductive load $V_{CE} = 400 \text{ V}, I_C = 15 \text{ A},$	T _c = 25 °C	—	400	—	ns
		V_{GE} = 15 V, R_{G} = 56 Ω See Fig. 6.2.1, 6.2.2	T _c = 175 °C	—	500	—	
Switching time (fall time)	t _f	Inductive load $V_{CE} = 400 \text{ V}, I_C = 15 \text{ A},$	T _c = 25 °C	_	40	_	ns
		V_{GE} = 15 V, R_G = 56 Ω See Fig. 6.2.1, 6.2.2	T _c = 175 °C	_	25	—	
Switching loss (turn-on switching loss)	E _{on}	Inductive load V_{CF} = 400 V, I _C = 15 A,	T _c = 25 °C	_	1.40	—	mJ
		V_{GE} = 15 V, R_G = 56 Ω See Fig. 6.2.1, 6.2.2	T _c = 175 °C		1.80	_	
Switching loss (turn-off switching loss)	E _{off}	Inductive load $V_{CE} = 400 \text{ V}, I_C = 15 \text{ A},$	T _c = 25 °C		0.22	_	mJ
		$V_{GE} = 15 \text{ V}, \text{R}_{G} = 56 \Omega$ See Fig. 6.2.1, 6.2.2	T _c = 175 °C		0.35	_	

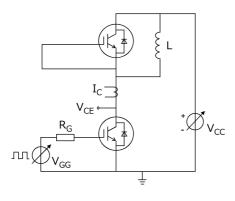


Fig. 6.2.1 Test Circuit

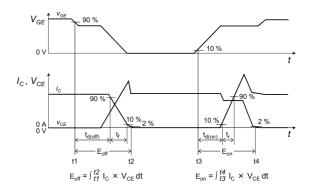


Fig. 6.2.2 Timing Chart

6.3. Diode Electrical Characteristics

Characteristics	Symbol	Test Condition		Min	Тур.	Max	Unit
Diode forward voltage	V _F	I _F = 15 A, V _{GE} = 0 V (pulse test)	T _c = 25 °C	_	1.20	1.50	V
			T _c = 175 °C	_	1.10	—	
Reverse recovery time		$V_{\rm R} = 400 \text{ V}, I_{\rm F} = 15 \text{ A},$	T _c = 25 °C	_	0.20	_	μS
		dl _F /dt = -500 A/µs See Fig.6.3.1, 6.3.2	T _c = 175 °C	_	0.27	_	
Reverce recovery charge	Q _{rr}	V _R = 400 V, I _F = 15 A, dI _F /dt = -500 A/μs See Fig.6.3.1, 6.3.2	T _c = 25 °C	_	3.5	_	μC
			T _c = 175 °C	_	5.0	_	
Peak reverce recovery current	I _{rr}	$V_{R} = 400 \text{ V}, I_{F} = 15 \text{ A},$	T _c = 25 °C	_	35	_	А
		dl _F /dt = -500 A/μs See Fig.6.3.1, 6.3.2	T _c = 175 °C	_	39	_	
Peak rate off fall of reverse recovery current	dl _F	V _R = 400 V, I _F = 15 A,	T _c = 25 °C	_	-350	_	A/μs
		dl _F /dt = -500 A/μs See Fig.6.3.1, 6.3.2	T _c = 175 °C	_	-310	_	

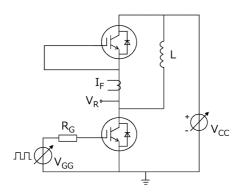
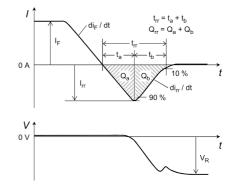


Fig. 6.3.1 Test Circuit





7. Marking (Note)

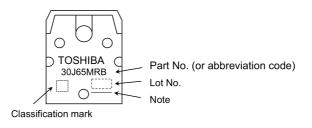


Fig. 7.1 Marking

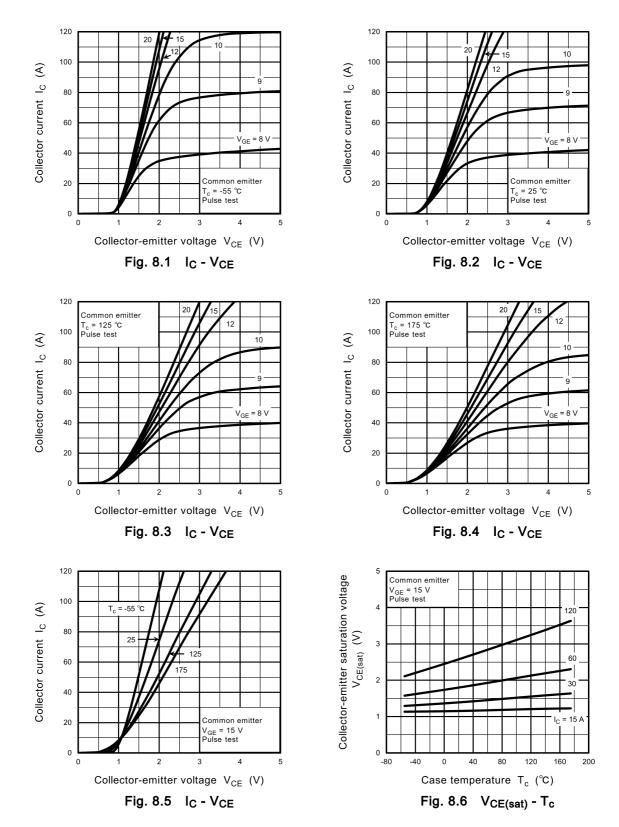
Note: A line under a Lot No. identifies the indication of product Labels. [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

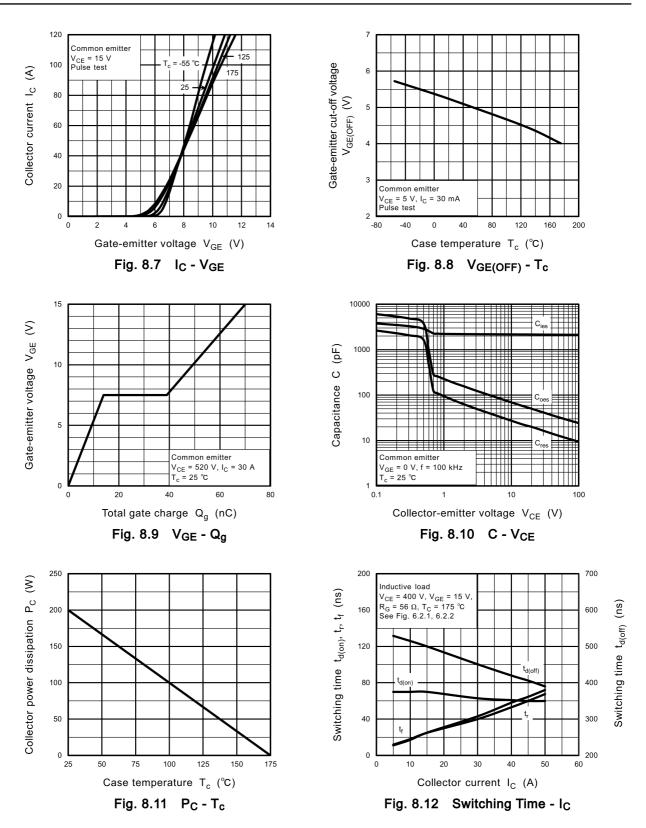
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

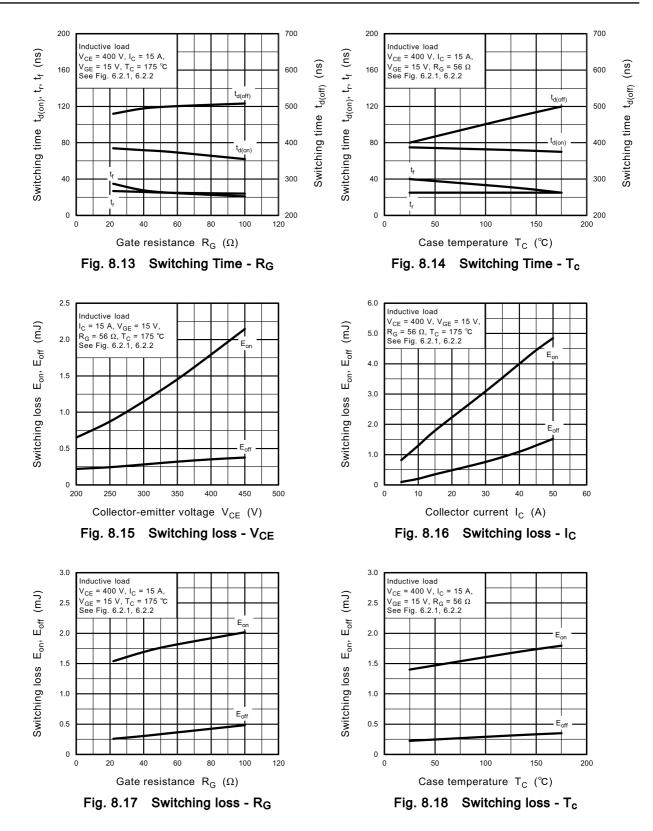
Note 1: This transistor is sensitive to electrostatic discharge and should be handled with care.

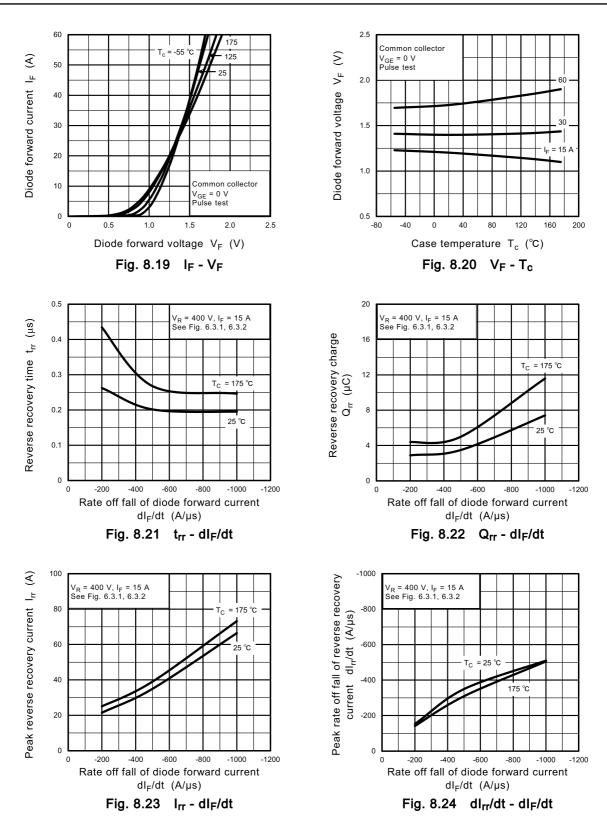
8. Characteristics Curves (Note)





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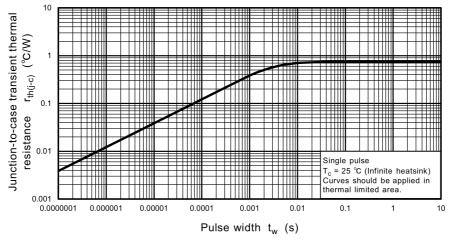
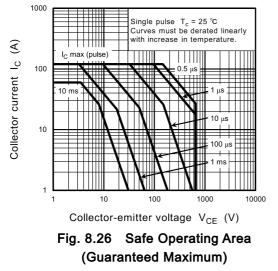


Fig. 8.25 $r_{th(j-c)}$ - t_w (Guaranteed Maximum)

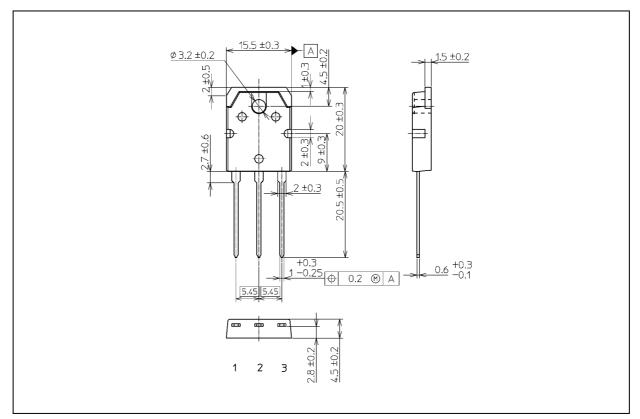


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

GT30J65MRB

Package Dimensions

Unit: mm



Weight: 4.6 g (typ.)

Package Name(s)	
TOSHIBA: 2-16C1S	
Nickname: TO-3P(N)	

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